EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	16138	((semiconductor) near3 (substrate\$1 or layer \$1)) near23 ((barrier) near2 (layer\$1 or substrate\$1))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/30 12:25
L2	80331	((semiconductor) near3 (substrate\$1 or layer \$1)) near23 ((drain or source or gate) near2 (contact\$1 or layer\$1 or substrate\$1))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/30 12:26
L3	142071	((semiconductor) near3 (substrate\$1 or layer \$1)) near23 ((insulator or insulating or dielectric or insulation) near2 (contact\$1 or layer\$1 or substrate\$1))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR		2009/12/30 12:27
L4	165	((semiconductor) near3 (substrate\$1 or layer \$1)) near23 ((insulator or insulating or dielectric or insulation) near2 (contact\$1 or layer\$1 or substrate\$1)) and ((change\$1 or changing or adjust\$1 or adjusting or modify\$1 or modifying or correct\$1 or correcting) near6 ((barrier) near3 (height or level)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/30 12:30
L5	2722	1 and 2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	····OFF	2009/12/30 12:30
L6	1751	3 and 5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/30 12:30

L7	12	4 and 6	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/30 12:31
L8	2097	((control\$1 or controlling or regulate\$1 or regulating) near5 ((height or conduction or conducting) near4 (barrier or electron\$1 or hole\$1)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/30 12:34
L9	42	4 and 8	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/30 12:34
L10	8	6 and 9	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/30 12:34
L11	10	(semiconductor adj3 layer) and (barrier adj3 layer) and (drain adj3 layer) and (source adj3 layer) and (drain adj3 contact) and (gate adj3 layer) and (insulator adj3 layer) and (active adj3 region)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/30 12:48
L12	4	(semiconductor adj3 layer) and (barrier adj3 layer) and (drain adj3 layer) and (source adj3 layer) and (drain adj3 contact) and (gate adj3 layer) and (insulator adj3 layer) and (active adj3 region) and (barrier adj3 height)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/12/30 12:49

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